

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Pomarede, et al.	) Group Art Unit: Unknown
App. No.	:	10/626,212	I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first-class mail in an envelope addressed to: Commissioner for
Filed	:	July 24, 2003	an envelope addressed by Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on
For	:	SURFACE PREPARATION PRIOR TO DEPOSITION	(Date)
Examiner	:	Unknown	Rabinder N. Narula, Reg. No. 53,371

## INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing twenty five (25) references that have been previously submitted by the Applicant and/or Examiner in a related Application (Serial Number 09/944,734 filed August 31, 2001) and additional copies are therefore not enclosed herewith in accordance with the provisions of 37 C.F.R. 1.98(d). This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBÉ, MÁRYENS, OLSON & BEAR, LLP

Bv:

Rabinder N. Narula Registration No. 53,371 Attorney of Record Customer No. 20,995 (949) 760-0404

(> 1>)

Dated

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PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE ATTY. DOCKET NO. ASMEX.284C1

APPLICATION NO. 10/626,212

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

APPLICANT Pomarede, et al.

(USE SEVERAL SHEETS IF NECESSARY)

FILING DATE
July 24, 2003
GROUP
Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1	2,394,930	2/12/46	McRae			
-	2	3,895,127	7/15/75	Comizzoli			
	3	4,056,642	11/1/77	Saxena et al.			
	4	4,292,343	9/29/81	Plaettner et al.	<del> </del>		
•	5	4,343,830	8/10/82	Sarma et al.	<del> </del> -		-
	6	4,436,761	3/13/84	Hayashi et al.			
,	7	4,544,571	10/1/85	Miller			
	8	4,645,683	2/24/87	Gourrier et al.	<del> </del>	<del> </del>	
	9	4,766,006	8/23/88	Gaczi	<u> </u>		
	10	5,135,775	8/4/92	Foller et al.		<u> </u>	
-	11	5,281,546	01/25/94	Possin et al.		<u> </u>	
	12	5,576,071	11/19/96	Sandhu	<u> </u>		
	13	5,587,205	12/24/96	Saito et al.			
	14	5,780,115	7/14/98	Park et al.		<u> </u>	
	15	5,939,763	08/17/99	Hao et al.			
	16	5,950,107	09/07/99	Huff et al.	_	<u> </u>	<u> </u>
	17	5,990,013	11/23/99	Berenguer et al.		<b></b>	
	18	5,993,916	11/30/99	Zhao et al.			
	19	6,107,192	08/22/00	Subrahmanyan et al.		<del></del>	<u> </u>
	20	6,200,866	03/13/01	Ma et al.			

	<u> </u>			FOREIGN PATENT DOCUMENTS	,			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
		Booding					YES	NO
	21	JP 60 254621 A	16.12.85	Patent Abstracts of Japan				
	22	JP 2000 160342 A	13.10.00	Patent Abstracts of Japan				
	23	0 617 461 A2	03/16/94	EPO				

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DATE CONSIDERED

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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DETTE V	FORM PTO-1449  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  TRADEMARK  TRADE	ATTY, DOCKET NO. ASMEX.284C1	APPLICATION NO. 10/626,212
	INFORMATION DISCLOSURE STATEMENT		
	BY APPLICANT	APPLICANT Pomarede, et al.	
	(USE SEVERAL SHEETS IF NECESSARY)	FILING DATE	GROUP
	(00202727	July 24, 2003	Unknown

EXAMINER	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)			
	Kim, H. and R. Reif, <i>Thin Solid Films</i> , Vol. 289:192-198 (1996), "In-situ low-temperature (600°C) wafer surface cleaning by electron cyclotron resonance hydrogen plasma"  Ramm J. and E. Beck, <i>Thin Solid Films</i> , Vol. 246:158-163 (1994), "Low temperature epitaxial growth by molecular beam epitaxy on hydrogen-plasma-cleaned silicon wafers."			

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